

SIPMOS® Power-Transistor

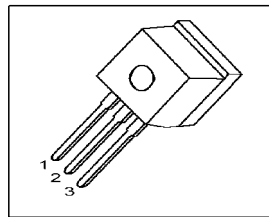
Feature

- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

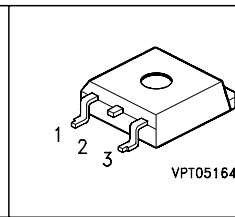
Product Summary

V_{DS}	100	V
$R_{DS(on)}$	14	mΩ
I_D	80	A

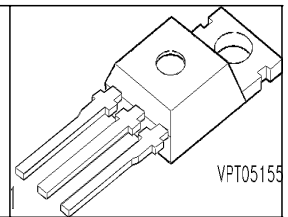
P-TO262-3-1



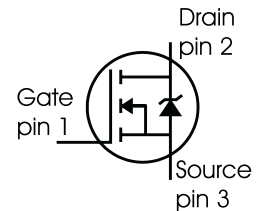
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP80N10L	P-TO220-3-1	Q67042-S4173	80N10L
SPB80N10L	P-TO263-3-2	Q67042-S4171	80N10L
SPI80N10L	P-TO262-3-1	Q67042-S4172	80N10L



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	80	A
$T_C = 25\text{ °C}$		58	
$T_C = 100\text{ °C}$			
Pulsed drain current	$I_{D\text{ puls}}$	320	
$T_C = 25\text{ °C}$			
Avalanche energy, single pulse	E_{AS}	700	mJ
$I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\text{ Ω}$			
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	25	
Reverse diode dv/dt	dv/dt	6	kV/μs
$I_S = 80\text{ A}$, $V_{DS} = 0\text{ V}$, $di/dt = 200\text{ A/μs}$			
Gate source voltage	V_{GS}	±20	V
Power dissipation	P_{tot}	250	W
$T_C = 25\text{ °C}$			
Operating and storage temperature	T_j , T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62.5	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ¹⁾		-	-	40	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=2mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 2\text{ mA}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^{\circ}C$ $V_{DS}=100V, V_{GS}=0V, T_j=150^{\circ}C$	I_{DSS}	- -	0.1 -	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	10	100	
Drain-source on-state resistance $V_{GS}=4.5V, I_D=58A$	$R_{DS(on)}$	-	15	24	m Ω
Drain-source on-state resistance $V_{GS}=10V, I_D=58A$	$R_{DS(on)}$	-	11	14	

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 58\text{A}$	26	52	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	3630	4540	pF
Output capacitance	C_{oss}		-	640	800	
Reverse transfer capacitance	C_{rss}		-	345	430	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 80\text{A}$, $R_G = 1.6\Omega$	-	14	21	ns
Rise time	t_r		-	60	90	
Turn-off delay time	$t_{d(off)}$		-	82	123	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

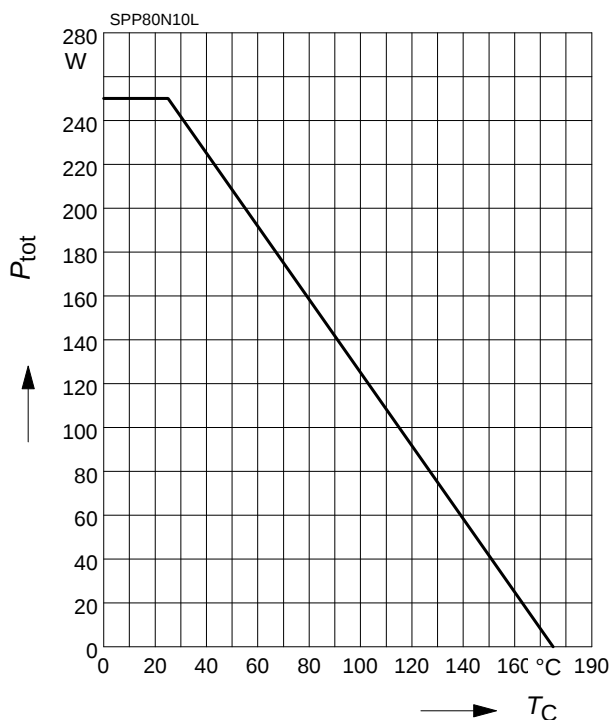
Gate to source charge	Q_{gs}	$V_{DD} = 80\text{V}$, $I_D = 80\text{A}$	-	14	21	nC
Gate to drain charge	Q_{gd}		-	65	98	
Gate charge total	Q_g	$V_{DD} = 80\text{V}$, $I_D = 80\text{A}$, $V_{GS} = 0 \text{ to } 10\text{V}$	-	160	240	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80\text{V}$, $I_D = 80\text{A}$	-	4.2	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ\text{C}$	-	-	80	A
Inv. diode direct current, pulsed	I_{SM}		-	-	320	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = 80\text{A}$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 50\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	95	140	ns
Reverse recovery charge	Q_{rr}		-	330	500	nC

1 Power dissipation

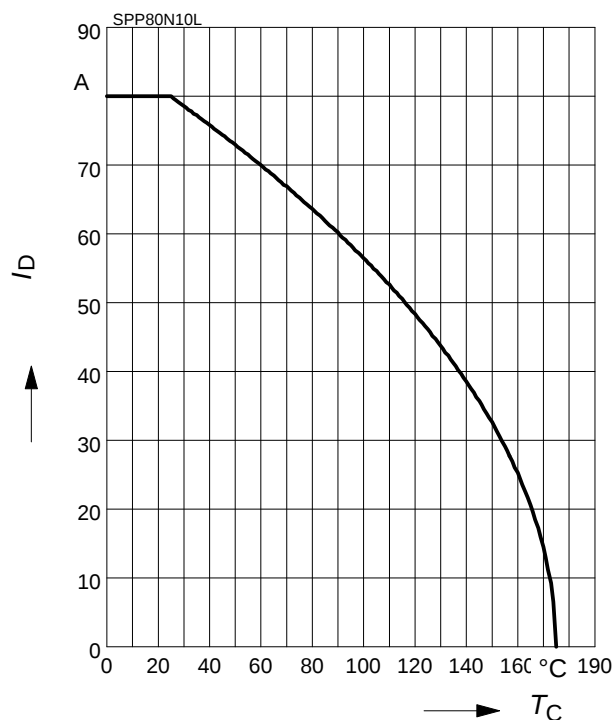
$$P_{\text{tot}} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

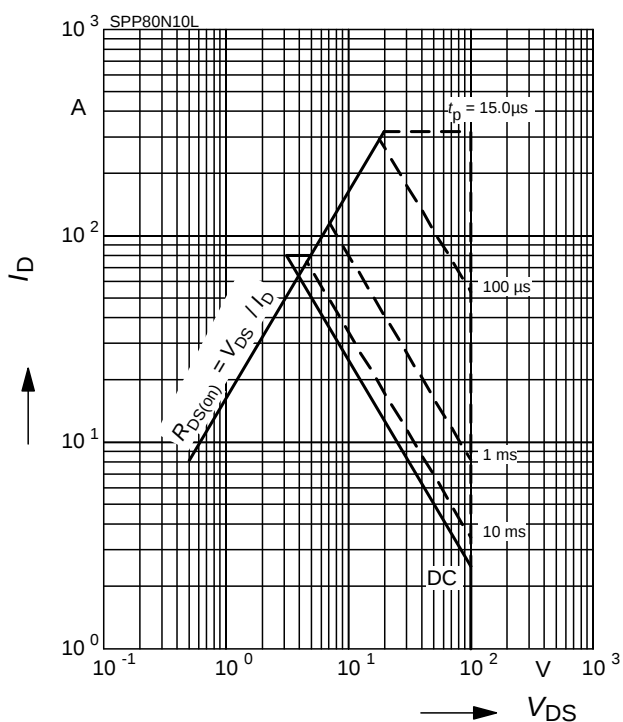
parameter: $V_{GS} \geq 10$ V



3 Safe operating area

$$I_D = f(V_{DS})$$

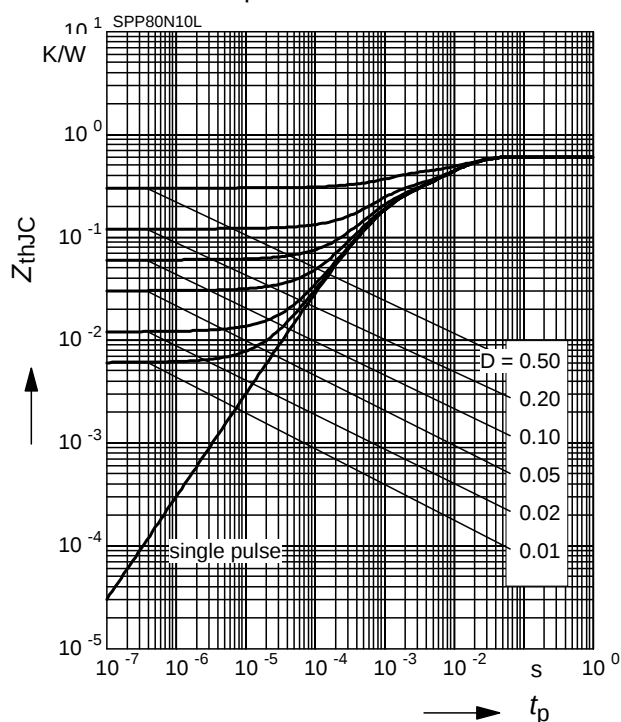
parameter: $D = 0$, $T_C = 25$ °C



4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

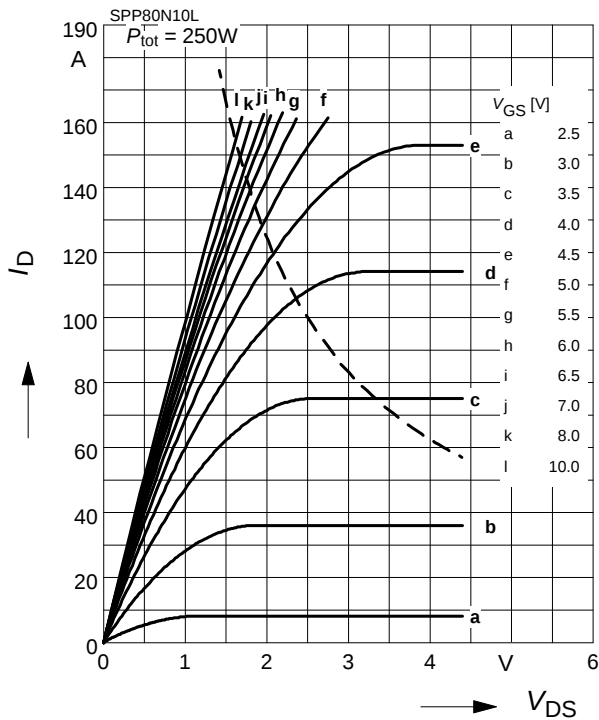
parameter: $D = t_p / T$



5 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

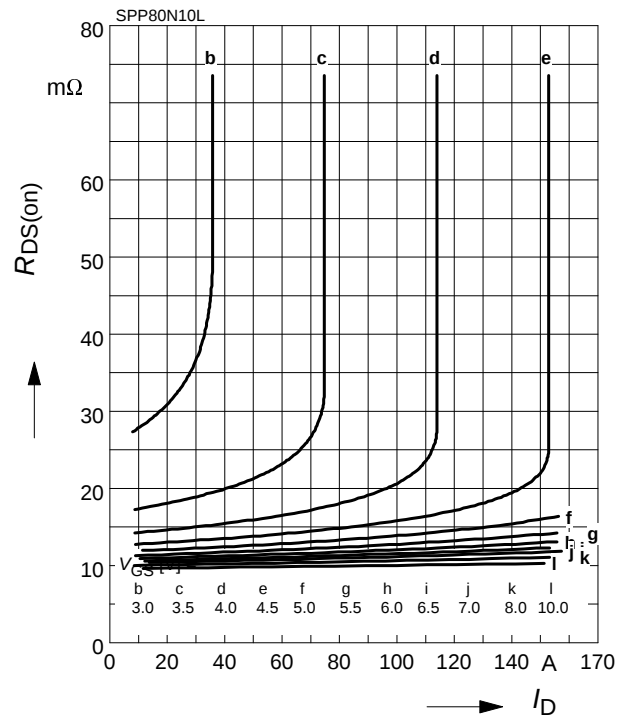
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

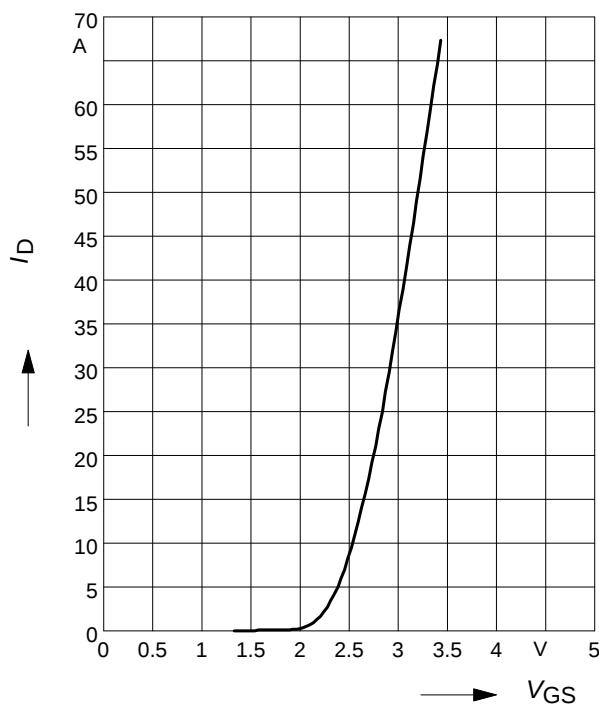
parameter: V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

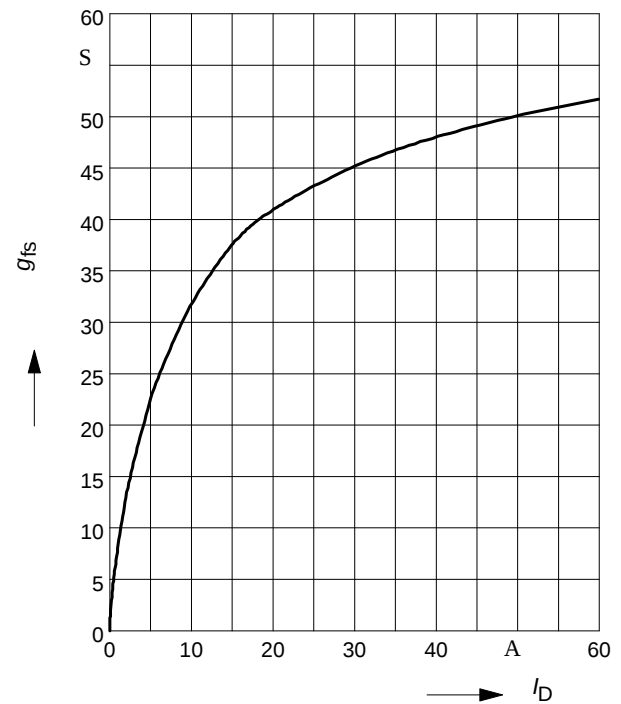
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

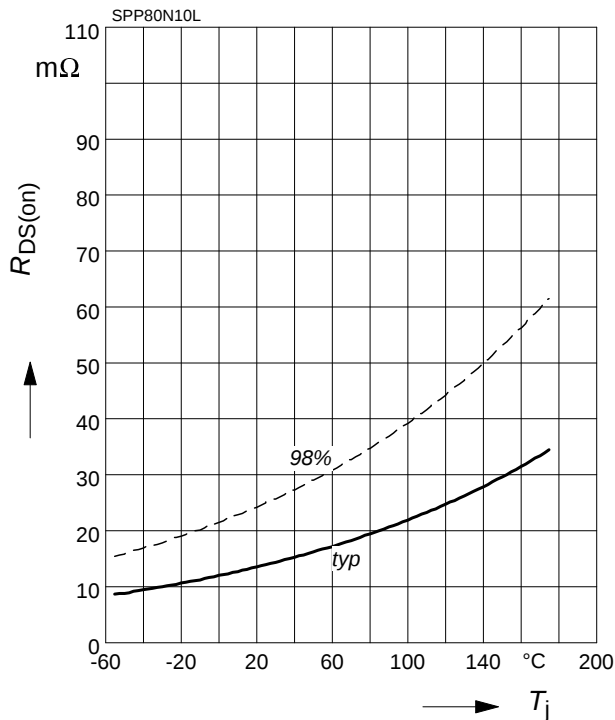
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

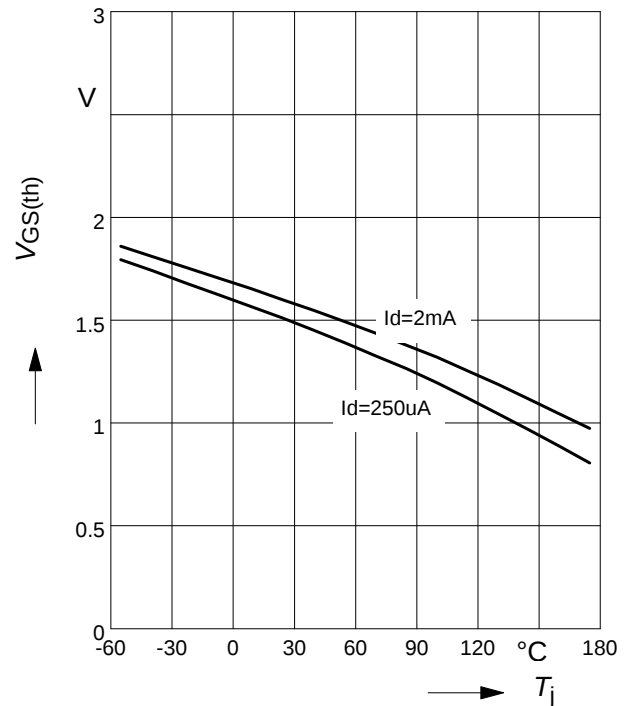
parameter: $I_D = 58 \text{ A}$, $V_{GS} = 4.5 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

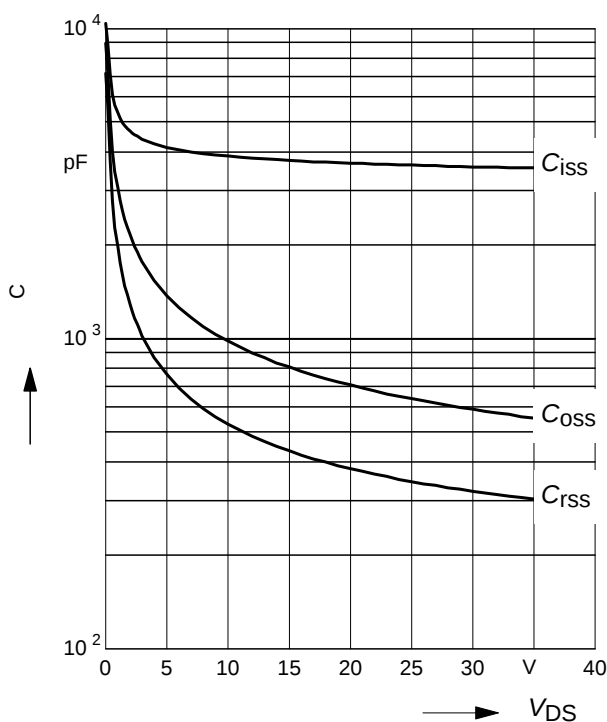
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

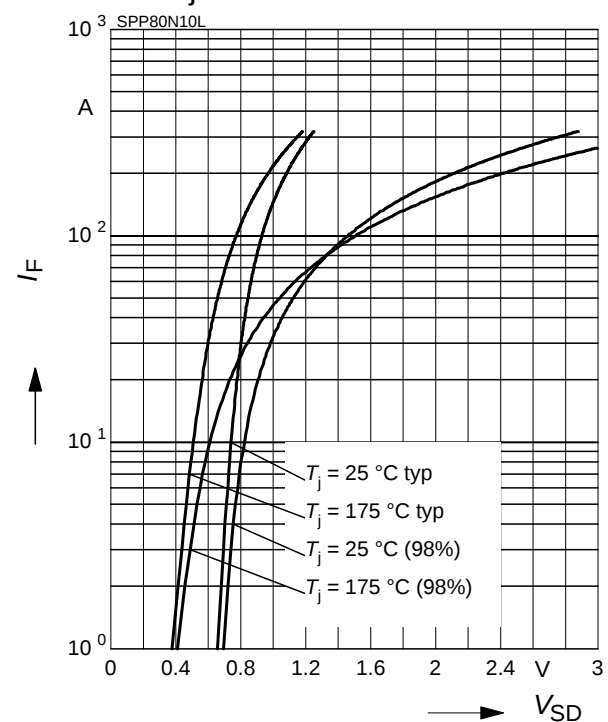
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

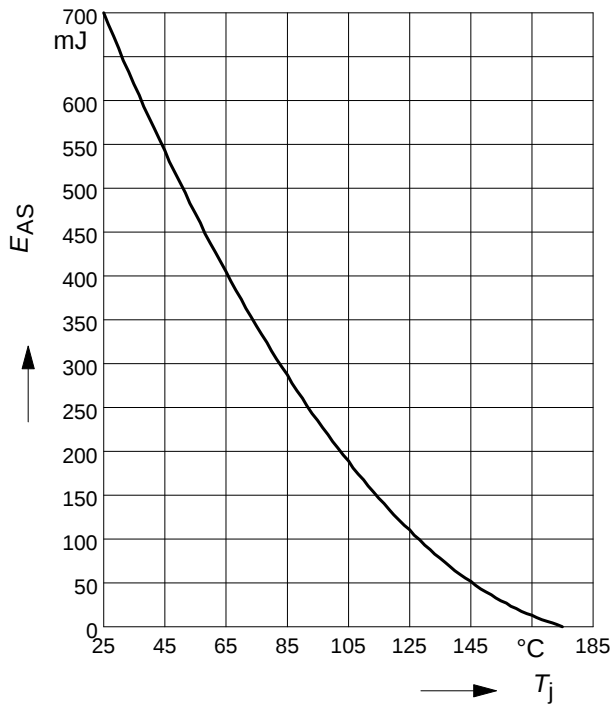
parameter: T_j , $t_p = 80 \mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

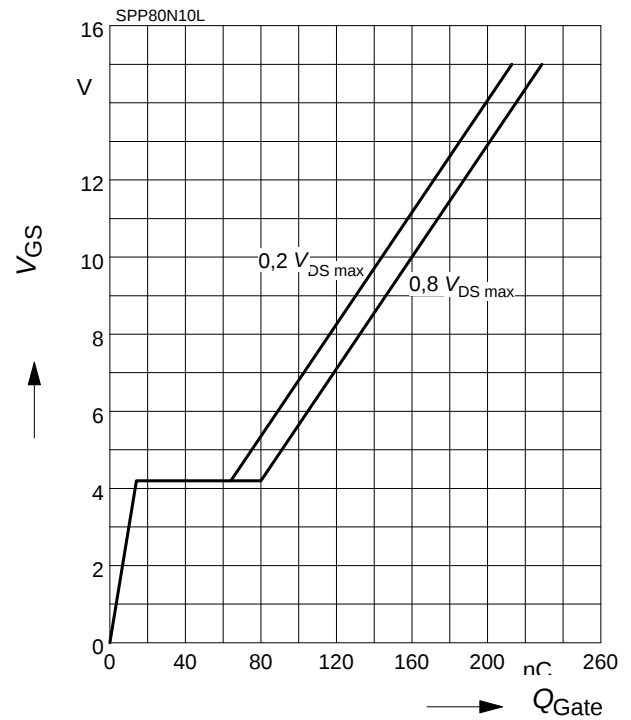
par.: $I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

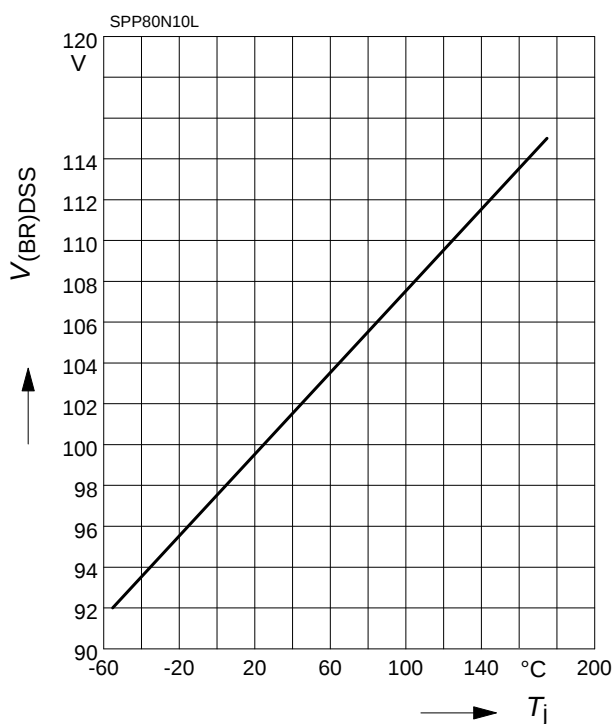
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 80\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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Further information

Please notice that the part number is BSPP80N10L, BSPB80N10L and BSPI80N10L, for simplicity the device is referred to by the term SPP80N10L, SPB80N10L and SPI80N10L throughout this documentation